

Alan C Farrell

List of Publications by Year in descending order

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875
citing authors

#	ARTICLE	IF	CITATIONS
1	Room-Temperature Midwavelength Infrared InAsSb Nanowire Photodetector Arrays with Al ₂ O ₃ Passivation. Nano Letters, 2019, 19, 2793-2802.	9.1	52
2	InGaAs GaAs Nanowire Avalanche Photodiodes Toward Single-Photon Detection in Free-Running Mode. Nano Letters, 2019, 19, 582-590.	9.1	40
3	Exploring time-resolved photoluminescence for nanowires using a three-dimensional computational transient model. Nanoscale, 2018, 10, 7792-7802.	5.6	7
4	Catalyst-free selective-area epitaxy of GaAs nanowires by metal-organic chemical vapor deposition using triethylgallium. Nanotechnology, 2018, 29, 085601.	2.6	16
5	Uncooled Photodetector at Short-Wavelength Infrared Using InAs Nanowire Photoabsorbers on InP with InP Heterojunctions. Nano Letters, 2018, 18, 7901-7908.	9.1	35
6	Axial InAs(Sb) inserts in selective-area InAsP nanowires on InP for optoelectronics beyond 25 Åµm. Optical Materials Express, 2018, 8, 1075.	3.0	12
7	Feasibility of room-temperature mid-wavelength infrared photodetectors using InAsSb nanostructured photoabsorbers. , 2018, , .		2
8	Seeding layer assisted selective-area growth of As-rich InAsP nanowires on InP substrates. Nanoscale, 2017, 9, 8220-8228.	5.6	16
9	Monolithic InGaAs Nanowire Array Lasers on Silicon-on-Insulator Operating at Room Temperature. Nano Letters, 2017, 17, 3465-3470.	9.1	91
10	Selective-area InAsSb Nanowires on InP for 3-5 Åµm Mid-wavelength Infrared Optoelectronics. MRS Advances, 2017, 2, 3565-3570.	0.9	7
11	Diode Characteristics Approaching Bulk Limits in GaAs Nanowire Array Photodetectors. Nano Letters, 2017, 17, 2420-2425.	9.1	25
12	Enhanced Carrier Multiplication in InAs Quantum Dots for Bulk Avalanche Photodetector Applications. Advanced Optical Materials, 2017, 5, 1601023.	7.3	10
13	Telecom-Wavelength Bottom-up Nanobeam Lasers on Silicon-on-Insulator. Nano Letters, 2017, 17, 5244-5250.	9.1	54
14	Nanopillar array band-edge laser cavities on silicon-on-insulator for monolithic integrated light sources. Applied Physics Letters, 2016, 108, .	3.3	14
15	Monolithically Integrated InGaAs Nanowires on 3D Structured Silicon-on-Insulator as a New Platform for Full Optical Links. Nano Letters, 2016, 16, 1833-1839.	9.1	69
16	High Quantum Efficiency Nanopillar Photodiodes Overcoming the Diffraction Limit of Light. Nano Letters, 2016, 16, 199-204.	9.1	38
17	Plasmonic field confinement for separate absorption-multiplication in InGaAs nanopillar avalanche photodiodes. Scientific Reports, 2015, 5, 17580.	3.3	21
18	High-Quality InAsSb Nanowires Grown by Catalyst-Free Selective-Area Metal-Organic Chemical Vapor Deposition. Nano Letters, 2015, 15, 6614-6619.	9.1	44

#	ARTICLE	IF	CITATIONS
19	Reflection spectromicroscopy for the design of nanopillar optical antenna detectors. , 2014, , .		2
20	Performance of IEEE 802.11 MAC in Underwater Wireless Channels. Procedia Computer Science, 2012, 10, 62-69.	2.0	5
21	Thin 3D Multiplication Regions in Plasmonically Enhanced Nanopillar Avalanche Detectors. Nano Letters, 2012, 12, 6448-6452.	9.1	39